

IN THE CLAIMS:

Please cancel claims 16-24 without prejudice or disclaimer to the subject matter contained therein.

Please amend claims 1-6, 8, and 15 as follows.

Claim 1. (Twice amended) A film acoustic wave device mounted at a position on a wafer comprising:

a ground electrode formed on the wafer;

a piezoelectric thin film formed on the ground electrode; and

at least one upper electrode formed on the piezoelectric thin film, wherein

at least the ground electrode, the piezoelectric thin film, and the at least one upper electrode form a pattern of the film acoustic wave device, and wherein

a shape of the pattern [shape] of the film acoustic wave device is [changed according to a] dependent upon the position [where] at which the film acoustic wave device is mounted on the wafer.

Claim 2. (Twice amended) The film acoustic wave device according to claim 1, wherein a length of the at least one upper electrode is [changed according to] dependent upon the position [where] at which the film acoustic wave device is mounted on the wafer.

F1
Cont

Claim 3. (Twice amended) The film acoustic wave device according to claim 1, wherein a width of the upper electrode is [changed according to] dependent upon the position [where] at which the film acoustic wave device is mounted on the wafer.

C1
Contd

Claim 4. (Twice amended) The film acoustic wave device according to claim 1 further including a plurality of upper electrodes, wherein distances between each of the plurality of upper electrodes are [changed according to] dependent upon the position [where] at which the film acoustic wave device is mounted on the wafer.

Claim 5. (Twice amended) The film acoustic wave device according to claim 1 further comprising:

a bonding pad for connecting with the at least one upper electrode, wherein

the pattern shape of the film acoustic wave device is formed by at least the ground electrode, the piezoelectric thin film, the at least one upper electrode, and the bonding pad, and wherein

a shape of the bonding pad is [changed according to] dependent upon the position [where] at which the film acoustic wave device is mounted on the wafer.

*F1
Cont*

Claim 6. (Twice amended) The film acoustic wave device according to claim 5 further comprising:

a connecting pattern for connecting the upper electrode with the bonding pad, wherein

the pattern shape of the film acoustic wave device is formed by at least the ground electrode, the piezoelectric thin film, the at least one upper electrode, the bonding pad, and the connecting pattern, and wherein

a shape of the connecting pattern is [changed according to] dependent upon the position [where] at which the film acoustic wave device is mounted on the wafer.

Cont'd

*SUB
F1
12*

Claim 8. (Twice amended) The film acoustic wave device according to claim 1 further comprising:

a capacitor provided on the same wafer as the film acoustic wave device, wherein

a capacitance of the capacitor is [changed according to] dependent upon the position [where] at which the film acoustic wave device is mounted on the wafer.

C3
Claim 15. (Twice amended) A circuit device mounted at a location on a substrate, comprising:

[a substrate; and]

at least one element [formed on the substrate] that forms a pattern shape of the device, wherein

[a] the pattern shape of [the at least one element formed on the substrate] the device is [changed according to a] dependent upon the position [where] at which the circuit device is mounted on the substrate.

Please add the following new claims.

--25. A film acoustic wave apparatus comprising:

a wafer; and

at least two film acoustic wave devices mounted at different positions on the wafer, each film acoustic wave device comprising:

C4
a ground electrode formed on the wafer;

a piezoelectric thin film formed on the ground electrode;

at least one upper electrode formed on the piezoelectric thin film;

and

a pattern formed by at least the ground electrode, the piezoelectric thin film, and the at least one upper electrode,

wherein

a shape of the pattern of at least one of the at least two film acoustic wave devices differs from a shape of the pattern of at least another of the at least two film acoustic wave device, according to the positions at which the film acoustic wave devices are mounted on the wafer.

26. A film acoustic wave device comprising: a semiconductor substrate made of one of a plurality of pieces into which a wafer is divided; a ground electrode formed on top of the semiconductor substrate; a piezoelectric thin film formed on top of the ground electrode; and an upper electrode formed on top of the piezoelectric thin film, wherein a pattern shape for the film acoustic wave device is changed by a position at the wafer.

27. The film acoustic wave device according to claim 26, wherein a length of the upper electrode is changed by the position at the wafer.

28. The film acoustic wave device according to claim 26, wherein a width of the upper electrode is changed by the position at the wafer.

29. The film acoustic wave device according to claim 26, wherein the upper electrode includes a plurality of upper electrodes, wherein distances between the upper electrodes are changed by the position at the wafer.

*SUB
E1
cancel*

30. The film acoustic wave device according to claim 26 further comprising a bonding pad for connecting with the upper electrode, wherein a shape of the bonding pad is changed by the position at the wafer.

*C4
cancel*

31. The film acoustic wave device according to claim 30 further comprising a connecting pattern for connecting the upper electrode with the bonding pad, wherein a shape of the connecting pattern is changed by the position at the wafer.

32. The film acoustic wave device according to claim 31, wherein the connecting pattern forms an air bridge.

*SUB
E2*

33. The film acoustic wave device according to claim 26 further comprising a capacitor provided on the same semiconductor substrate as the film acoustic wave device, wherein a capacitance of the capacitor is changed by the position of the wafer.

*SUB
E2
cont.*

34. The film acoustic wave device according to claim 26, wherein the semiconductor substrate is made of gallium arsenide (GaAs); the piezoelectric thin film is made of lead titanate (PbTiO₃); and at least one of the upper electrode is a conductor substantially made of platinum (Pt).

*34
cont'd*

35. The film acoustic wave device according to claim 26, wherein the a semiconductor substrate is made of silicon (Si); the piezoelectric thin film is made of lead titanate (PbTiO₃); and at least one of the upper electrode is a conductor substantially made of platinum (Pt).

36. The film acoustic wave device according to claim 26, wherein the piezoelectric thin film is made of PZT (PbTiO₃-PbZrO₃); and at least one of the upper electrode and the ground electrode is a conductor substantially made of platinum (Pt).

37. The film acoustic wave device according to claim 26, wherein the piezoelectric thin film is made of zinc oxide (ZnO).

38. The film acoustic wave device according to claim 26, wherein the piezoelectric thin film is made of aluminum nitride (AlN).

Sub E2 amended.
14 cancelled
39. The film acoustic wave device according to claim 26 further comprising an inductor between the semiconductor substrate and the ground electrode.

Sub D1
40. A circuit device comprising: a substrate; and a plurality of elements formed on the substrate, wherein the pattern shape of the elements formed on the substrate is changed by a position at the substrate.--

REMARKS

Claims 1-15 and 25-40 are pending in the present application. Claims 1-6, 8, and 15 have been amended. Claims 25-40 have been added, and claims 16-24 have been cancelled. Claims 1, 15, 25, 26 and 40 are independent claims.

Applicants respectfully submit that claims 1-6, 8, and 15 have been amended in order to more clearly recite the structural features of the present invention and to ensure compliance with 35 U.S.C. §112(2).

STATUS OF CLAIM 24

In the Office Action dated September 13, 2000, the Examiner stated in the Office Action Summary (PTO-326) that claims 16-24 are withdrawn from consideration. Applicants respectfully submit that claim 24 should not have